

ERRATUM | JULY 29 2020

Erratum: "Characterization of two-dimensional hexagonal boron nitride using scanning electron and scanning helium ion microscopy" [Appl. Phys. Lett. 104, 031607 (2014)] **FREE**

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In the original published article,¹ an error appeared in Eq. (1) and should correctly read as follows:

$$I_s(\tilde{n}) = C_{\text{BN}}I_p(0) \frac{1 - (D_p D_s)^{\tilde{n}}}{1 - D_p D_s} + C_{\text{Sub}}I_p(0)(D_p D_s)^{\tilde{n}} + C_{\text{BG}}I_p(0). \quad (1)$$

Another error appeared in the text between Eqs. (2) and (3) (Ref. 1) and should be correctly read as follows:

$$\text{where } A_0 = \left(C_{\text{BG}} + \frac{C_{\text{BN}}}{1 - D_p D_s} \right) I_p(0), \quad A_1 = \left(C_{\text{Sub}} - \frac{C_{\text{BN}} D_p D_s}{1 - D_p D_s} \right) I_p(0), \quad \text{and}$$

The errors have no effect on the rest of the article or the conclusion of the paper.

We sincerely apologize for these oversights.

REFERENCE

¹H. Guo, J. Gao, N. Ishida, M. Xu, and D. Fujita, *Appl. Phys. Lett.* **104**, 031607 (2014).